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April 1st, 2010 Renesas Electronics Corporation

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MOS INTEGRATED CIRCUIT $\mu PD3768$

7500 PIXELS $\times\,3$ COLOR CCD LINEAR IMAGE SENSOR

DESCRIPTION

The μ PD3768 is a high-speed and high sensitive color CCD (Charge Coupled Device) linear image sensor which changes optical images to electrical signal and has the function of color separation.

The μ PD3768 has 3 rows of 7500 pixels, and it is a 2-output/color type CCD sensor with 2 rows/color of charge transfer register, which transfers the photo signal electrons of 7500 pixels separately in odd and even pixels. Therefore, it is suitable for 600 dpi/A3 high-speed color digital copiers, color scanners and so on.

FEATURES

| Valid photocell | : 7500 pixels $	imes$ 3 |
|--------------------------------------|--|
| Photocell pitch | : 9.325 µm |
| Line spacing | : 37.3 μ m (4 lines) Red line - Green line, Green line - Blue line |
| Color filter | : Primary colors (red, green and blue), pigment filter (with light resistance 10 ⁷ lx•hour) |
| Resolution | : 24 dot/mm A3 (297 $	imes$ 420 mm) size (shorter side) |
| Drive clock level | : CMOS output under 5 V operation |
| Data rate | : 44 MHz MAX. (22 MHz/1 output) |
| Output type | : 2 outputs in phase/color |
| Power supply | : +10 V |
| On-chip circuits | : Reset feed-through level clamp circuits |
| | Voltage amplifiers |

ORDERING INFORMATION

| Part Number | Package |
|-------------|--|
| μPD3768D-AZ | CCD linear image sensor 36-pin ceramic DIP (CERDIP) (15.24 mm (600)) |

<R> **Remark** The μ PD3768D-AZ is a lead-free product.

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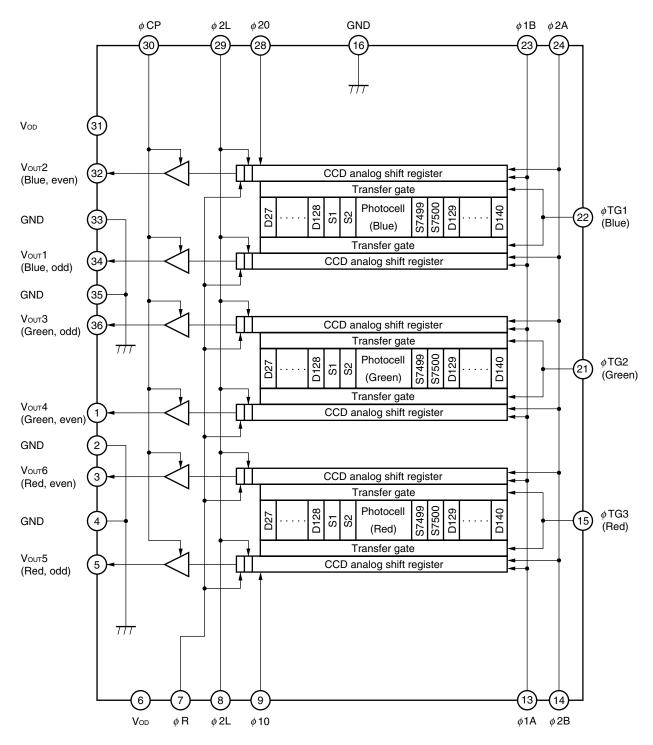
Document No. S15418EJ3V0DS00 (3rd edition) Date Published February 2006 NS CP (N) Printed in Japan

The mark <R> shows major revised points.

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The revised points can be easily searched by copying an "<R>" in the PDF file and specifying it in the "Find what:" field.

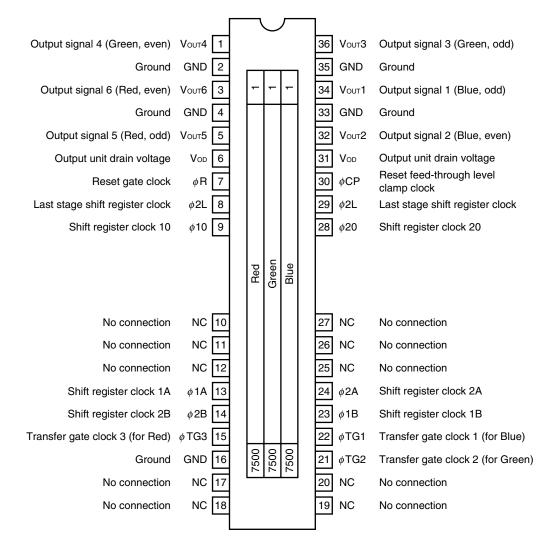
BLOCK DIAGRAM



PIN CONFIGURATION (Top View)

CCD linear image sensor 36-pin ceramic DIP (CERDIP) (15.24 mm (600))

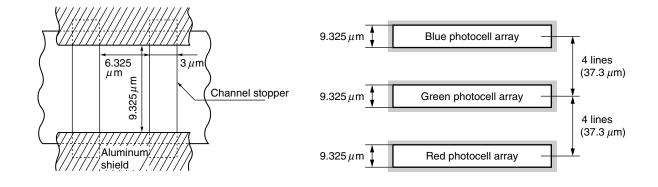
• μPD3768D-AZ



Caution Connect the No connection pins (NC) to GND.

PHOTOCELL STRUCTURE DIAGRAM

PHOTOCELL ARRAY STRUCTURE DIAGRAM (Line spacing)



ABSOLUTE MAXIMUM RATINGS (TA = +25°C)

| Parameter | Symbol | Ratings | Unit |
|--|----------------|-------------|------|
| Output drain voltage | Vod | -0.3 to +12 | V |
| Shift register clock voltage | Vø1, Vø2 | -0.3 to +8 | V |
| Last gate shift register clock voltage | Vø2L | -0.3 to +8 | V |
| Reset gate clock voltage | Vør | -0.3 to +8 | V |
| Clamp clock voltage | Vøcp | -0.3 to +8 | V |
| Transfer gate clock voltage | Vøtgi to Vøtgi | -0.3 to +8 | V |
| Operating ambient temperature Note | Та | -25 to +60 | °C |
| Storage temperature | Tstg | -40 to +100 | °C |

Note Use at the condition without dew condensation.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

| Parameter | Symbol | Min. | Тур. | Max. | Unit |
|---|----------------------------|------|----------------------|---------------|------|
| Output drain voltage | Vod | 9.5 | 10.0 | 10.5 | V |
| Shift register clock high level | Vø1H, Vø2H | 4.5 | 5.0 | 5.5 | V |
| Shift register clock low level | $V_{\phi 1L}, V_{\phi 2L}$ | -0.3 | 0 | +0.5 | V |
| Last gate shift register clock high level | Vø2LH | 4.5 | 5.0 | 5.5 | V |
| Last gate shift register clock low level | Vø2LL | -0.3 | 0 | +0.5 | V |
| Reset gate clock high level | Vørh | 4.5 | 5.0 | 5.5 | V |
| Reset gate clock low level | Vø RL | -0.3 | 0 | +0.5 | V |
| Clamp clock high level | Vøcрн | 4.5 | 5.0 | 5.5 | V |
| Clamp clock low level | VØCPL | -0.3 | 0 | +0.5 | V |
| Transfer gate clock high level | Vøтg1н to Vøтg3н | 4.5 | V∉1H ^{Note} | Vø 1H Note | V |
| Transfer gate clock low level | Vøtg1l to Vøtg3l | -0.3 | 0 | +0.5 | V |
| Data rate | 2f _ø R | 1 | 2 | 44 | MHz |

RECOMMENDED OPERATING CONDITIONS (TA = +25°C)

Note When Transfer gate clock high level ($V_{\phi TG1H}$ to $V_{\phi TG3H}$) is higher than Shift register clock high level ($V_{\phi 1H}$), Image lag can increase.

ELECTRICAL CHARACTERISTICS

 $T_A = +25^{\circ}C$, $V_{OD} = 10$ V, $f_{\phi R} = 1$ MHz, data rate = 2 MHz, storage time = 10 ms, input signal clock = 5 V_{p-p} , light source (except Response1) : 2950 K halogen lamp + CM-500S (infrared cut filter, t = 1 mm)

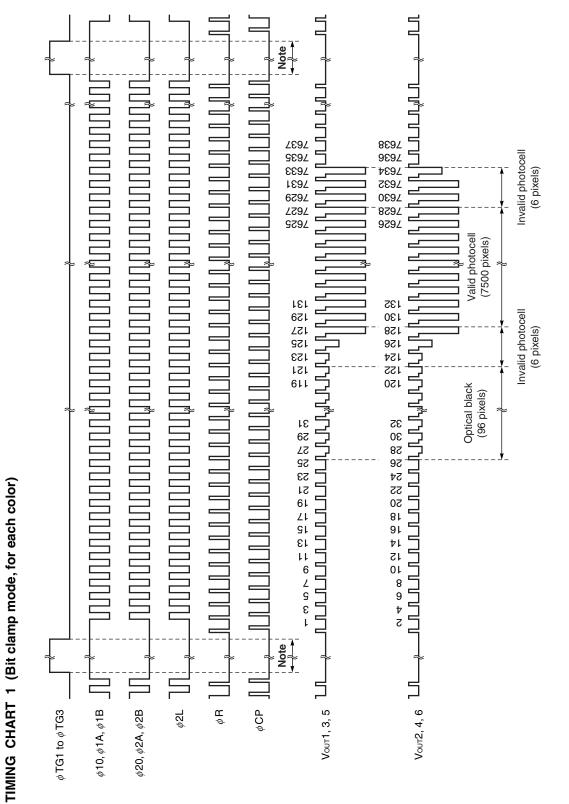
| Parameter | | Symbol | Test Conditions | Min. | Тур. | Max. | Unit |
|-------------------------------|-------|----------------|---|-------|------|------|--------|
| Saturation voltage | | Vsat | | 1.5 | 2.0 | - | V |
| Saturation exposure | Red | SER | 2950 K halogen lamp + CM-500S | - | 0.14 | - | lx•s |
| | Green | SEG | | - | 0.13 | - | lx•s |
| | Blue | SEB | | _ | 0.26 | _ | lx•s |
| Photo response non-unifo | mity | PRNU | Vout = 1.0 V | _ | 6.0 | 18.0 | % |
| Photo response non-unifor | mity | PRNU2 | Vout = 0.1 V | - | 6.0 | 18.0 | % |
| at low illumination | | | | | | | |
| Average dark signal | | ADS | Light shielding, data rate = 2 MHz, storage time = 10 ms | _ | 1.0 | 5.0 | mV |
| Dark signal non-uniformity | | DSNU | Light shielding, data rate = 2 MHz, storage time = 10 ms | - | 3.0 | 12.0 | mV |
| Power consumption | | Pw | - | _ | 700 | 900 | mW |
| Output impedance | | Zo | | _ | 0.2 | 0.4 | kΩ |
| Response1 | Red | R _R | 3200 K halogen lamp + C-500S | 15.4 | 22.0 | 28.6 | V/lx•s |
| | Green | Rg | + HA-50 | 12.6 | 18.0 | 23.4 | V/lx•s |
| | Blue | Rв | | 5.6 | 8.0 | 10.4 | V/lx•s |
| Response2 | Red | RR | 2950 K halogen lamp + CM-500S | 9.8 | 14.0 | 18.2 | V/lx•s |
| | Green | Rg | | 10.7 | 15.3 | 19.9 | V/lx•s |
| | Blue | Rв | | 5.3 | 7.6 | 9.9 | V/lx•s |
| Image lag | | IL | Vout = 500 mV | _ | 40 | 80 | mV |
| Image lag color difference | | IL-DIF | Vout = 500 mV | _ | 5 | 20 | mV |
| Image lag O/E | | IL-O/E | Vout = 500 mV | _ | 10 | 30 | mV |
| Offset level Note 1 | | Vos | | 3.8 | 4.5 | 5.2 | V |
| Output fall delay time Note 2 | | td | | _ | 14 | _ | ns |
| Register imbalance | | RI | Vout = 1.0 V | _ | 0 | 5 | % |
| Total transfer efficiency | | TTE | Vout = 1.0 V, før = 22 MHz | 94 | 98 | _ | % |
| Response peak | Red | | | - | 630 | _ | nm |
| | Green | | | | 540 | _ | nm |
| | Blue | | | - | 445 | _ | nm |
| Dynamic range | | DR1 | Vsat/DSNU | _ | 666 | _ | times |
| | | DR2 | V _{sat} / σ dark | _ | 870 | _ | times |
| Reset feed-through noise | | RFTN | Light shielding | -1000 | -200 | +500 | mV |
| Light shielding random noise | | σ dark | Bit clamp, t17 = 10 ns | _ | 2.3 | _ | mV |

Notes 1. Refer to TIMING CHART 2 and TIMING CHART 4.

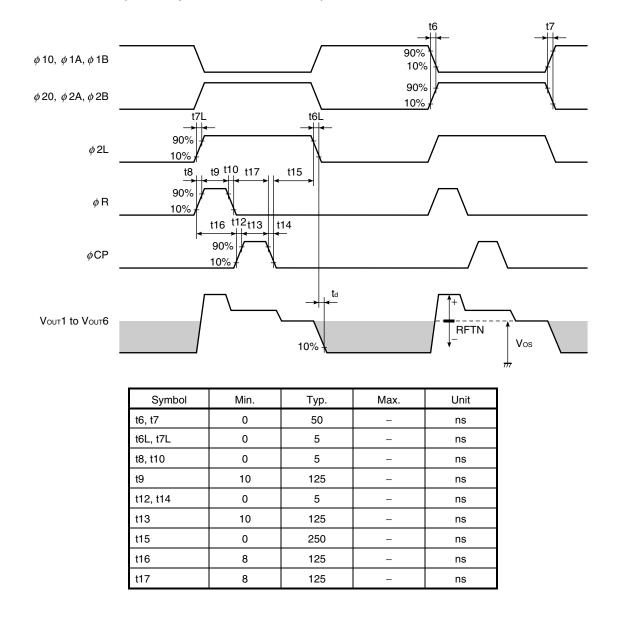
2. td is defined as periods from 10% of ϕ 2L to 10% of Vout1 to Vout6 (refer to APPLICATION CURCUIT EXAMPLE).

INPUT PIN CAPACITANCE (TA = +25°C, VoD = 10 V)

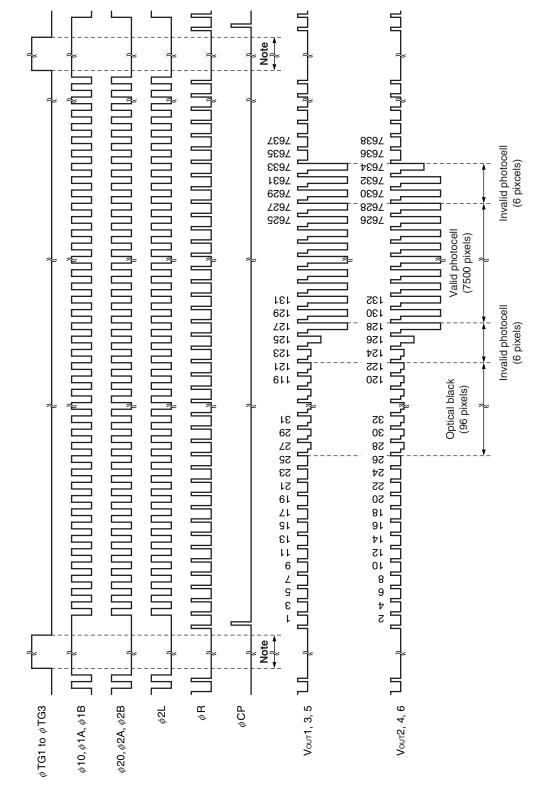
| Parameter | Symbol | Pin | Pin No. | Min. | Тур. | Max. | Unit |
|---|-----------------|-------------|---------|------|------|------|------|
| Shift register clock pin capacitance | Cø1 | <i>φ</i> 10 | 9 | _ | 330 | 450 | pF |
| | | <i>φ</i> 1A | 13 | - | 330 | 450 | pF |
| | | <i>φ</i> 1Β | 23 | - | 330 | 450 | pF |
| | C _{¢2} | φ2B | 14 | _ | 330 | 450 | pF |
| | | <i>φ</i> 2A | 24 | _ | 330 | 450 | pF |
| | | <i>φ</i> 20 | 28 | _ | 330 | 450 | pF |
| Last stage shift register clock pin capacitance | Cøl | <i>ø</i> 2L | 8 | _ | 10 | 20 | pF |
| | | | 29 | - | 10 | 20 | pF |
| Reset gate clock pin capacitance | Cør | φR | 7 | - | 10 | 20 | pF |
| Clamp clock pin capacitance | Cøcp | φCP | 30 | _ | 10 | 20 | pF |
| Transfer gate clock pin capacitance | Cøtg | ¢TG1 | 22 | _ | 100 | 150 | pF |
| | | φTG2 | 21 | _ | 100 | 150 | pF |
| | | φTG3 | 15 | _ | 100 | 150 | pF |



Note Set the ϕR and ϕCP pulse to low level during this period.

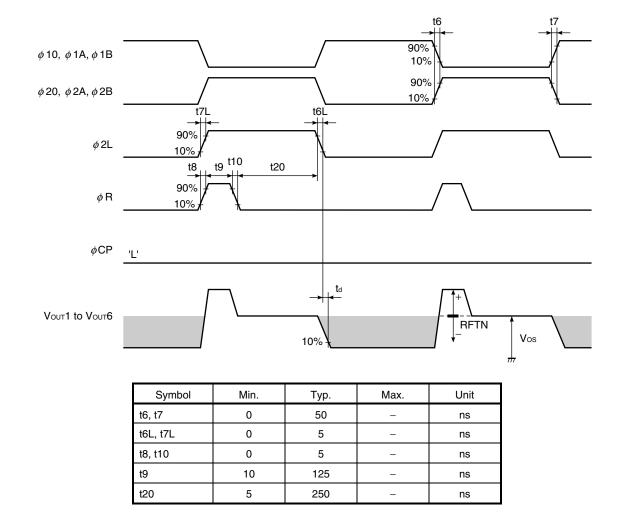


TIMING CHART 2 (Bit clamp mode, for each color)



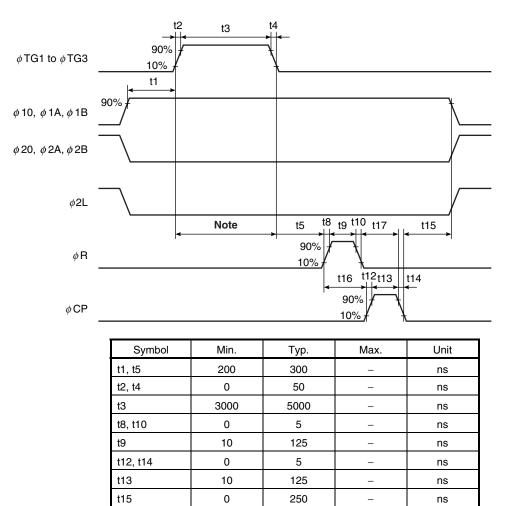
TIMING CHART 3 (Line clamp mode, for each color)

Note Set the ϕR and ϕCP pulse to low level during this period.



TIMING CHART 4 (Line clamp mode, for each color)

TIMING CHART 5 (Bit clamp mode, line clamp mode, for each color)



Note Set the ϕ R and ϕ CP pulse to low level during this period.

8

8

125

125

_

_

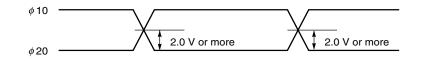
ns

ns

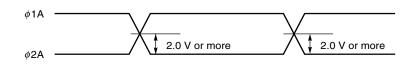
t16

t17

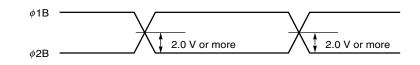
*\phi*10, *\phi*20 cross points



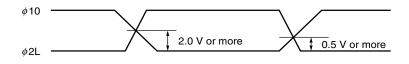
ø1A, ø2A cross points



ϕ 1B, ϕ 2B cross points



ϕ 10, ϕ 2L cross points



Remark Adjust cross points (ϕ 10, ϕ 20), (ϕ 1A, ϕ 2A), (ϕ 1B, ϕ 2B) and (ϕ 10, ϕ 2L) with input resistance of each pin.

DEFINITIONS OF CHARACTERISTIC ITEMS

- Saturation voltage : V_{sat}
 Output signal voltage at which the response linearity is lost.
- 2. Saturation exposure : SE

Product of intensity of illumination (Ix) and storage time (s) when saturation of output voltage occurs.

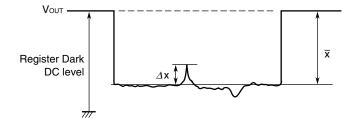
3. Photo response non-uniformity : PRNU

The output signal non-uniformity of all the valid pixels when the photosensitive surface is applied with the light of uniform illumination. This is calculated by the following formula, and it is defined by each six of them.

PRNU (%) =
$$\frac{\Delta x}{\overline{x}} \times 100$$

 $\Delta x : \text{maximum of } |x_j - \overline{x}|$
 $\overline{x} = \frac{\sum_{j=1}^{7500} x_j}{7500}$

x_j : Output voltage of valid pixel number j



4. Average dark signal : ADS

Average output signal voltage of all the valid pixels at light shielding. This is calculated by the following formula, and it is defined by each six of them.

ADS (mV) =
$$\frac{\sum_{j=1}^{7500} d_j}{7500}$$

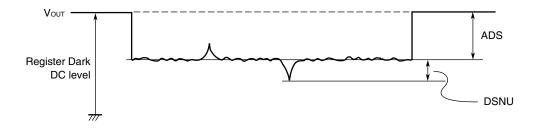
dj : Dark signal of valid pixel number j

5. Dark signal non-uniformity : DSNU

Absolute maximum of the difference between ADS and voltage of the highest or lowest output pixel of all the valid pixels at light shielding. This is calculated by the following formula, and it is defined by each six of them.

DSNU (mV) : maximum of $|d_j - ADS|_{j=1 \text{ to } 7500}$

dj : Dark signal of valid pixel number j



6. Output impedance : Zo

Impedance of the output pins viewed from outside.

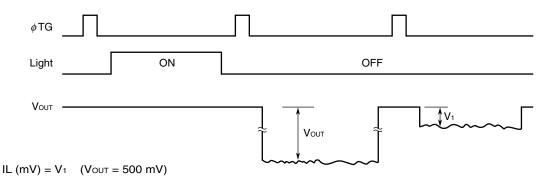
7. Response : R

Output voltage divided by exposure (lx•s).

Note that the response varies with a light source (spectral characteristic).

8. Image lag : IL

The rate between the last output voltage and the next one after read out the data of a line.



9. Image lag color difference : IL-DIF

It is defined as a difference between colors of the average of image lag.

It is expressed with the next expression to be concrete.

| (average of image lag of blue output) – (average of image lag of green output) |
 | (average of image lag of green output) – (average of image lag of red output) |
 | (average of image lag of red output) – (average of image lag of blue output) |

10. Image lag O/E : IL-O/E

It is defined as a difference of the average of image lag of odd and even pixels for each color.

11. Register imbalance : RI

The rate of the difference between the averages of the output voltage of Odd and Even pixels, against the average output voltage of all the valid pixels.

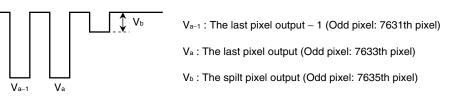
$$\mathsf{RI} (\%) = \frac{\frac{2}{n} \left| \sum_{j=1}^{\frac{n}{2}} (V_{2j-1} - V_{2j}) \right|}{\frac{1}{n} \sum_{j=1}^{n} V_j} \times 100$$

n : Number of valid pixels V_i : Output voltage of each pixel

12. Total transfer efficiency : TTE

The total transfer rate of CCD analog shift register. This is calculated by the following formula, it is difined by each output.

TTE (%) = $(1 - V_b / \text{average output of all the valid pixels}) \times 100$

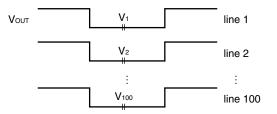


13. Light shielding random noise : $\sigma dark$

Light shielding random noise σ dark is defined as the standard deviation of a valid pixel output signal with 100 times (=100 lines) data sampling at dark (light shielding).

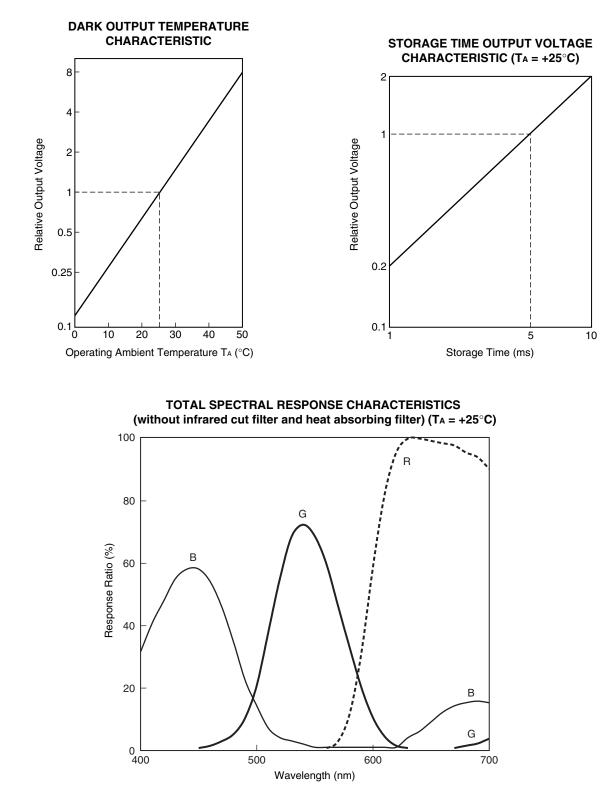
$$\sigma$$
 dark (mV) = $\sqrt{\frac{\sum_{i=1}^{100} (V_i - \overline{V})^2}{100}}$, $\overline{V} = \frac{1}{100} \sum_{i=1}^{100} V_i$

Vi: A valid pixel output signal among all of the valid pixels for each color

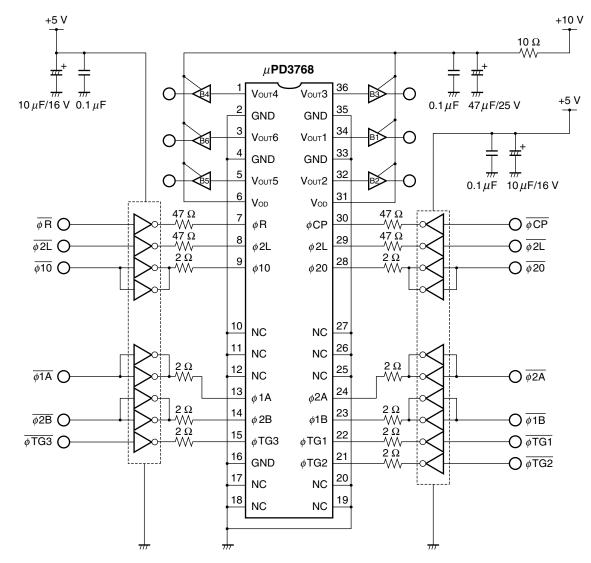


This is measured by the DC level sampling of only the signal level, not by CDS (Correlated Double Sampling).

STANDARD CHARACTERISTIC CURVES (Reference Value)



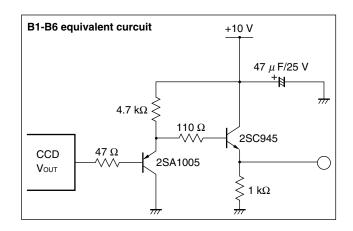
APPLICATION CIRCUIT EXAMPLE



Caution Connect the No connection pins (NC) to GND.

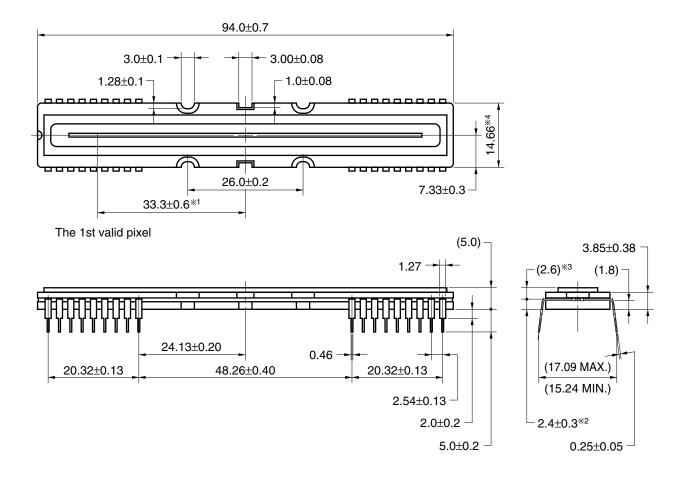
Remarks 1. Connect two inverters (74AC04) to each ϕ 10, ϕ 1A, ϕ 1B, ϕ 2O, ϕ 2A, ϕ 2B pin.

- 2. Inverters shown in the above application circuit example are the 74AC04.
- 3. B1 to B6 in the application circuit example are shown in the figure below.



PACKAGE DRAWING

CCD LINEAR IMAGE SENSOR 36-PIN CERAMIC DIP (15.24 mm (600))



| Name | Dimension | Refractive index |
|-----------|--------------|------------------|
| Glass cap | 91.0×9.0×1.1 | 1.5 |

- ※1 1st valid pixel → Center of package
- % 2 The bottom of package ---- The surface of the chip
- *3 The surface of the chip \leftarrow The surface of the glass cap
- % 4 The tolerance of packge dimension ± 0.25 : less than 10 mm from W/F edge ± 0.50 : equal or more than 10 mm from W/F edge

36D-1CCD-PKG3-1

RECOMMENDED SOLDERING CONDITIONS

When soldering this product, it is highly recommended to observe the conditions as shown below. If other soldering processes are used, or if the soldering is performed under different conditions, please make sure to consult with our sales offices.

Type of Through-hole Device

µPD3768D-AZ : CCD linear image sensor 36-pin ceramic DIP (CERDIP) (15.24 mm (600))

| Process | Conditions |
|------------------------|--|
| Partial heating method | Pin temperature : 300 °C or below, Heat time : 3 seconds or less (per pin) |

- Cautions 1. During assembly care should be taken to prevent solder or flux from contacting the glass cap. The optical characteristics could be degraded by such contact.
 - 2. Soldering by the solder flow method may have deleterious effects on prevention of glass cap soiling and heat resistance. So the method cannot be guaranteed.

NOTES ON HANDLING THE PACKAGES

(1) MOUNTING OF THE PACKAGE

The application of an excessive load to the package may cause the package to warp or break, or cause chips to come off internally. Particular care should be taken when mounting the package on the circuit board. Don't have any object come in contact with glass cap. You should not reform the lead frame. We recommended to use a IC-inserter when you assemble to PCB.

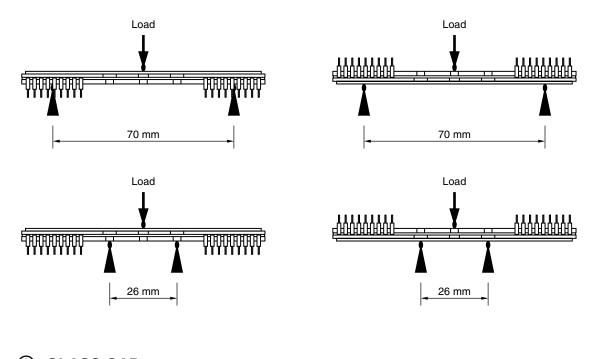
Also, be care that the any of the following can cause the package to crack or dust to be generated.

- 1. Applying heat to the external leads for an extended period of time with soldering iron.
- 2. Applying repetitive bending stress to the external leads.
- 3. Rapid cooling or heating

For this product, the reference value for the three-point bending strength ^{Note} is 180 [N] (at distance between supports: 70 mm), is 500 [N] (at distance between supports: 26 mm). Avoid imposing a load, however, on the inside portion as viewed from the face on which the window (glass) is bonded to the package body (ceramic).

Note Three-point bending strength test

Distance between supports: 70 mm or 26 mm, Support R: R 2 mm, Loading rate: 0.5 mm/min.



② GLASS CAP

Don't either touch glass cap surface by hand or have any object come in contact with glass cap surface. Care should be taken to avoid mechanical or thermal shock because the glass cap is easily to damage. For dirt stuck through electricity ionized air is recommended.

NEC

NOTES ON HANDLING THE PACKAGES

③ OPERATE AND STORAGE ENVIRONMENTS

Operate in clean environments. CCD image sensors are precise optical equipment that should not be subject to mechanical shocks. Exposure to high temperatures or humidity will affect the characteristics. So avoid storage or usage in such conditions.

Keep in a case to protect from dust and dirt. Dew condensation may occur on CCD image sensors when the devices are transported from a low-temperature environment to a high-temperature environment. Avoid such rapid temperature changes.

For more details, refer to our document "Review of Quality and Reliability Handbook" (C12769E)

④ ELECTROSTATIC BREAKDOWN

CCD image sensor is protected against static electricity, but destruction due to static electricity is sometimes detected. Before handling be sure to take the following protective measures.

- 1. Ground the tools such as soldering iron, radio cutting pliers of or pincer.
- 2. Install a conductive mat or on the floor or working table to prevent the generation of static electricity.
- 3. Either handle bare handed or use non-chargeable gloves, clothes or material.
- 4. Ionized air is recommended for discharge when handling CCD image sensor.
- 5. For the shipment of mounted substrates, use box treated for prevention of static charges.
- 6. Anyone who is handling CCD image sensors, mounting them on PCBs or testing or inspecting PCBs on which CCD image sensors have been mounted must wear anti-static bands such as wrist straps and ankle straps which are grounded via a series resistance connection of about 1 MΩ.

[MEMO]

NOTES FOR CMOS DEVICES -

1 VOLTAGE APPLICATION WAVEFORM AT INPUT PIN

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (MAX) and V_{IH} (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (MAX) and V_{IH} (MIN).

(2) HANDLING OF UNUSED INPUT PINS

Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.

③ PRECAUTION AGAINST ESD

A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.

④ STATUS BEFORE INITIALIZATION

Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.

⑤ POWER ON/OFF SEQUENCE

In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current.

The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.

6 INPUT OF SIGNAL DURING POWER OFF STATE

Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.

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